

L Number	Hits	Search Text	DB	Time stamp
1	43	(trenches and etch\$3 and (silicon-on-insulator)).clm.	USPAT; US-PGPUB	2003/08/29 11:22
-	565	(216/2).CCLS.	USPAT; US-PGPUB	2003/05/09 16:46
-	178	electrostatic same comb adj drive	USPAT; US-PGPUB	2002/10/24 15:45
-	470	etch adj stop adj material	USPAT; US-PGPUB	2002/10/24 15:54
-	107	(trenches and (etch-stop or etch adj stop)).clm.	USPAT; US-PGPUB	2003/08/29 11:21
-	179	release adj etch\$3	USPAT; US-PGPUB	2002/10/28 14:41
-	55	(release adj etch\$3)and (trench or trenches)	USPAT; US-PGPUB	2002/10/28 11:45
-	544	release near2 etch\$3	USPAT; US-PGPUB	2002/10/28 11:17
-	48	(release adj etch\$3)and (trench or trenches)and (mask or masking)	USPAT; US-PGPUB	2002/10/28 11:45
-	247	(216/11).CCLS.	USPAT; US-PGPUB	2002/10/28 12:09
-	865	(438/424).CCLS.	USPAT; US-PGPUB	2002/10/28 12:10
-	131	(438/412).CCLS.	USPAT; US-PGPUB	2002/10/28 12:10
-	181	(438/739).CCLS.	USPAT; US-PGPUB	2002/10/28 12:10
-	192	(438/740).CCLS.	USPAT; US-PGPUB	2002/10/28 12:11
-	58	release same etch\$3 same mask\$3 same trench	USPAT; US-PGPUB	2002/10/28 14:44
-	563	release same etch\$3 same mask\$3	USPAT; US-PGPUB	2002/10/28 14:44
-	311	(MEMS or "MEM's") and (etch\$3 or releas\$) and (void or cavity) and (bond\$3 near3 wafer)	USPAT; US-PGPUB	2003/05/09 15:51
-	50	("4861420" "4882933" "4904978" "4993143" "5060526" "5062302" "5084408" "5198390" "5231301" "5313836" "5326726" "5343064" "5355712" "5445988" "5447067" "5461922" "5476819" "5495761" "5503285" "5504026" "5506175" "5511428" "5537872" "5569852" "5574222" "5576250" "5578755" "5592015" "5602052" "5616523" "5627317" "5627318" "5631422" "5706565" "5719069" "5719073" "5723353" "5747353" "5747867" "5756901" "5798283" "5847280" "5847454" "5850042" "5882532" "5949144" "5959208" "6121552" "6013933" "6239473").PN.	USPAT	2003/05/09 16:09
-	411	(MEMS or microstructure\$1 or microelectromechanical) and (wafer adj bonding)	USPAT; US-PGPUB	2003/08/28 17:02
-	50	216/2 and etch-stop	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:33
-	125	216/2 and accelerometer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:35
-	27	216/2 and accelerometer and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 17:05

-	16	216/2 and (filling and trenches).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:55
-	1360	(MEMS or microstructure\$1 or microelectromechanical) and trenc\$2	USPAT; US-PGPUB	2003/08/28 17:02
-	76	(MEMS or microstructure\$1 or microelectromechanical) and trenc\$2 and etch-stop	USPAT; US-PGPUB	2003/08/28 17:03
-	311	216/2 and trench\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 17:06
-	183	216/2 and trench\$2 and fill\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 17:07